

Description

The NDS9430 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

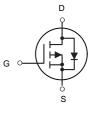
S S S G

SOP-8 (SOIC-8)

General Features

 $V_{DS} = -30 V I_{D} = -5.8 A$

 $R_{DS(ON)}$ < 55 m Ω @ V_{GS} =10V



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NDS9430	SOP-8(SOIC-8)	HXY MOSFET	3000

Absolute Maximum Ratings(Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	- 30	V
VGS	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Drain Current ³ , V _{GS} @ 10V	-5.8	А
IDM	Pulsed Drain Current ¹	-20	А
P _D @T _A =25°C	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	50	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -30		-33	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS} (th)	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	-1	-1.6	-3	V
		V _{GS} =-10V, I _D =-5.1A	-	43	55	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =-4.5V, I _D =-4.2A	-	62	90	mΩ
Forward Transconductance	gFS	V _{DS} =-15V,I _D =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)	1		"			
Input Capacitance	Clss		-	520	-	PF
Output Capacitance	Coss	V _{DS} =-15V,V _{GS} =0V,	-	130	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	70	-	PF
Switching Characteristics (Note 4)	1					
Turn-on Delay Time	td(on)		-	7	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-1A,	-	13	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =-10V, R_{GEN} =6 Ω	-	14	-	nS
Turn-Off Fall Time	tf		-	9	-	nS
Total Gate Charge	Qg		-	11	-	nC
Gate-Source Charge	Qgs	V _{DS} =-15V,I _D =-5.1A, V _{GS} =-10V	-	2.2	-	nC
Gate-Drain Charge	Q _{gd}	V 00 10 V	-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V, I _S =-5.1A	-	-	-1.2	V

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

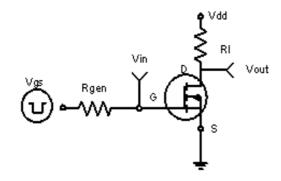


Figure 1:Switching Test Circuit

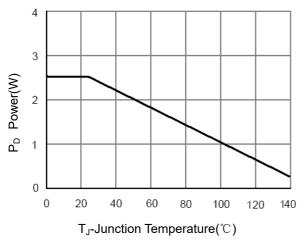


Figure 3 Power Dissipation

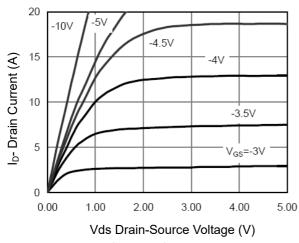


Figure 5 Output Characteristics

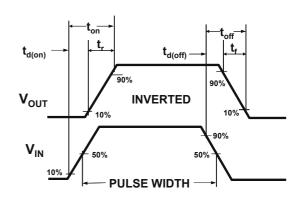


Figure 2:Switching Waveforms

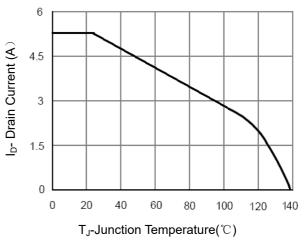


Figure 4 Drain Current

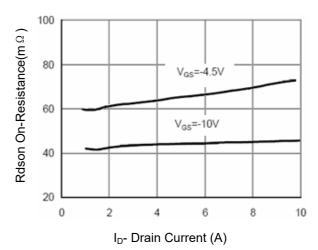
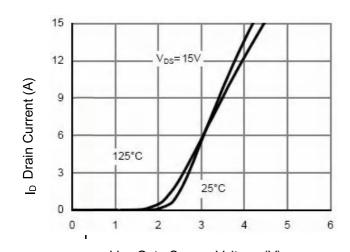
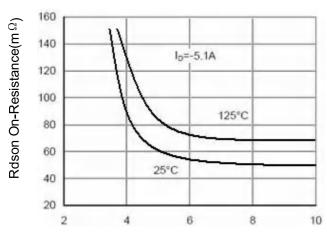


Figure 6 Drain-Source On-Resistance

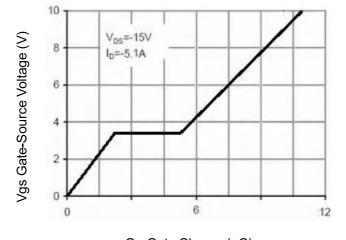




Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Qg Gate Charge (nC) Figure 11 Gate Charge

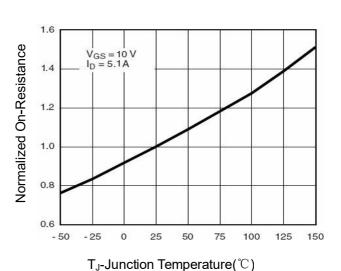
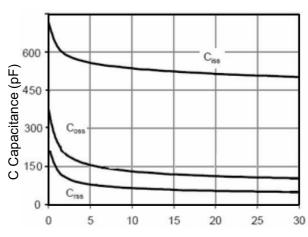
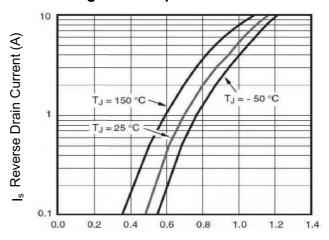


Figure 8 Drain-Source On-Resistance

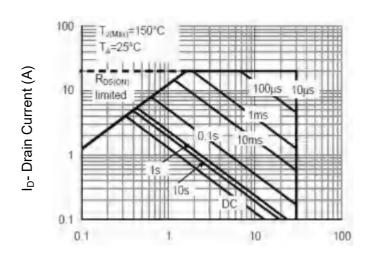


Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



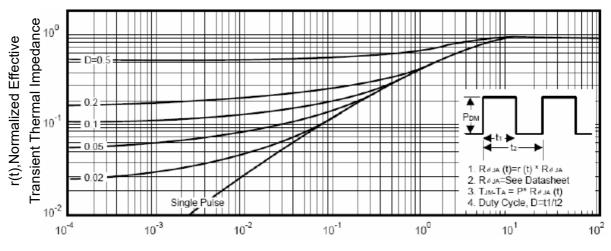
Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

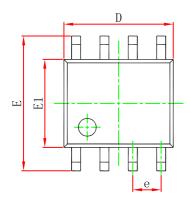


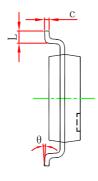
Square Wave Pluse Duration(sec)

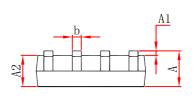
Figure 14 Normalized Maximum Transient Thermal Impedance



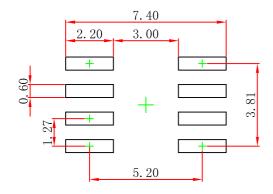
SOP-8(SOIC-8) Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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